

# ELEC2208 Power Electronics and Drives

## Extra slides

Yoshi Tsuchiya  
Smart Electronic Materials and Systems (SEMS) Group  
59/4219  
[yt2@ecs.soton.ac.uk](mailto:yt2@ecs.soton.ac.uk)

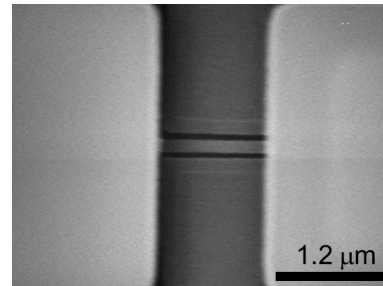
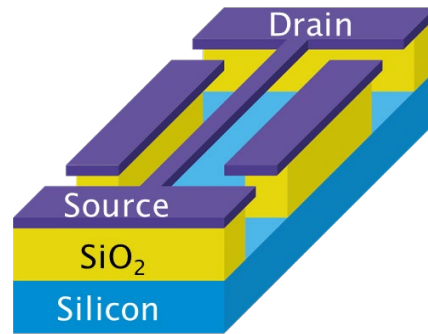
# My research link with Power Electronics

Topic

## Nanoelectromechanical Systems (NEMS)

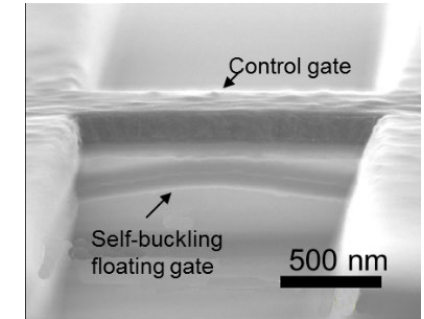
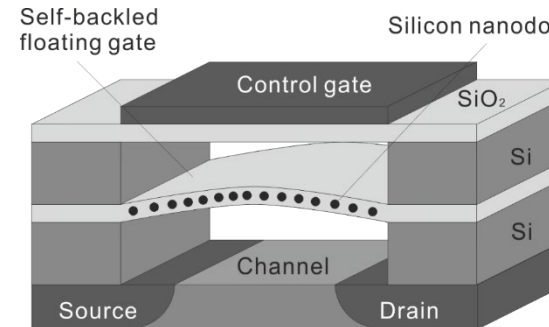
### NEMS Resonator

Y. Tsuchiya et al., IEEE MEMS2018



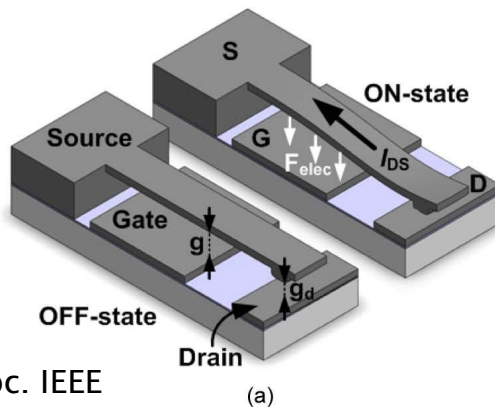
### NEMS memory

Y. Tsuchiya et al, JAP 2006

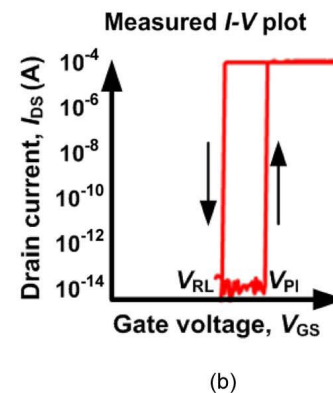


## MEMS/NEMS switches for power management ➔ Towards “Ideal switch”!

### Contact switches

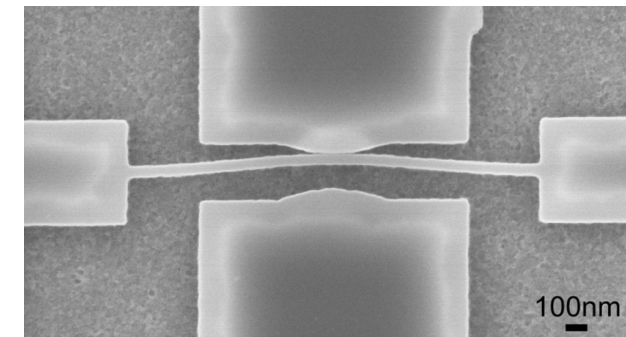


V. Pott et al., Proc. IEEE 98, 2076 (2010).



### Energy-reversible low-power NEMS switches

Boodhoo, Tsuchiya *et al.*, Microelec. Eng. 2015.

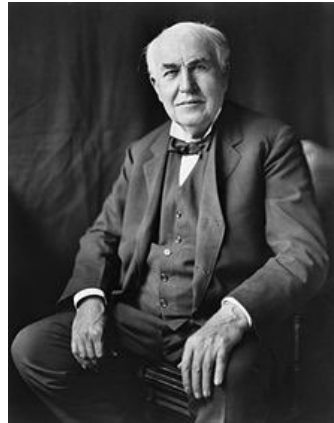


# Diode – History

Topic



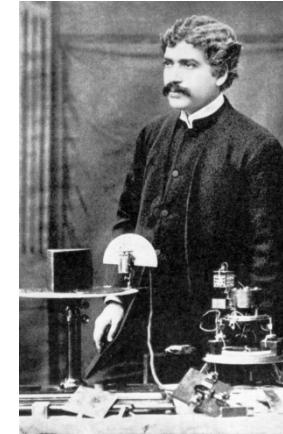
F. Guthrie  
British physicist  
(1873)



T. Edison  
American inventor  
(1880)

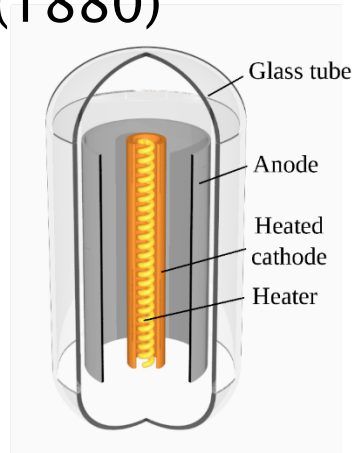


K. F. Braun  
German engineer  
(1874)



J. C Bose  
Indian scientist  
(1894)

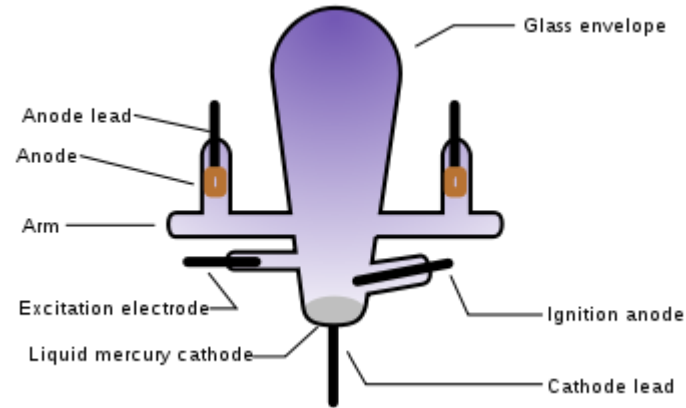
Vacuum tube  
diode



Solid state diode

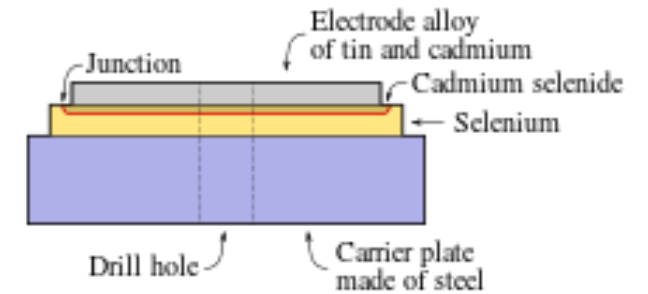
Contact between metal and  
mineral/crystal

## Mercury-arc rectifier



- Invented by American engineer Peter Cooper Hewitt in 1902.
- Cold cathode gas-filled tube.
- For high-voltage and high current.

## Selenium rectifier



- Manufactured from 1930s
- Metal (CdSe) – Semiconductor (Se) junction

Then superseded by silicon rectifier in 1970s.



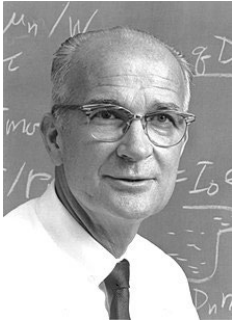
# Thyristor - History

Topic

- PNP switches developed at Bell laboratories.

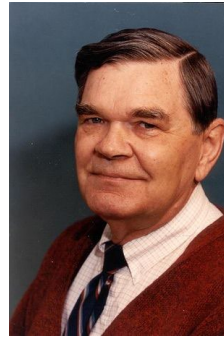
<https://en.wikipedia.org/wiki/Thyristor>

<https://www.tdworld.com/digital-innovations/hvdc/article/20969683/a-short-history-on-the-thyristor-valve>



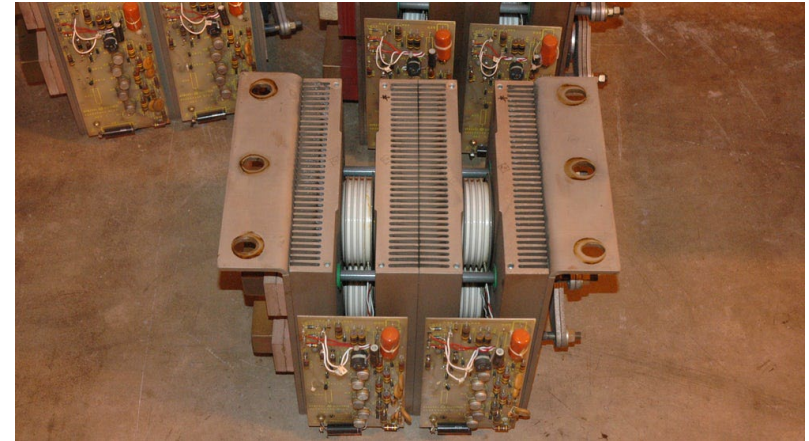
Proposal

W. Shockley



Team leader

J. Moll



- Commercialised by General Electric (GE) in 1957.
- “Thyratron” + “Transistor” = “Thyristor”
- Dawn of “Power Electronics”



Frank “Bill” Gutzwiller



# Power MOSFET - History

Topic

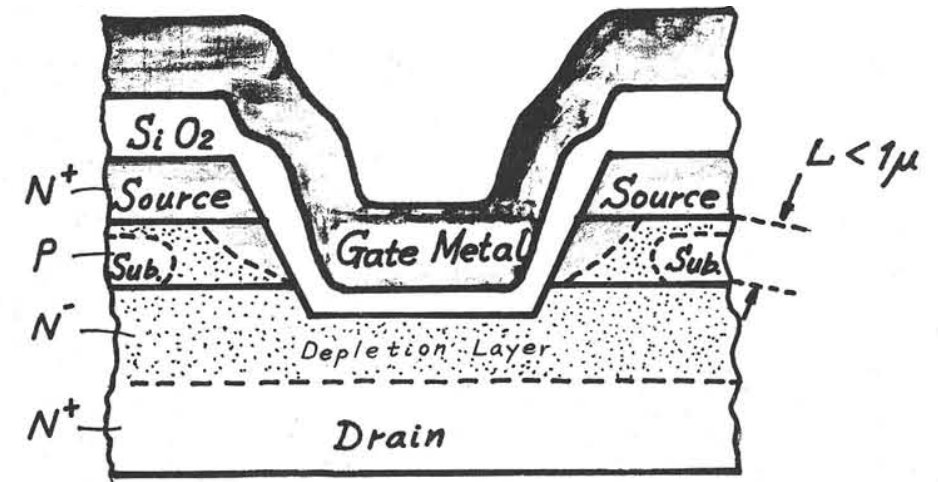
MOSFET was invented by Atalla and Kahng at Bell Labs, US in 1959.

[https://en.wikipedia.org/wiki/Power\\_MOSFET](https://en.wikipedia.org/wiki/Power_MOSFET)

Tarui et al., SSDM 1969

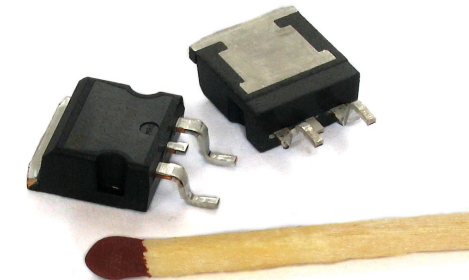
## Power MOSFET was invented in 1969

- Hitachi invented a basis of VMOS (Vertical MOS)
- Yasuo Tarui et al (ETL, Japan) invented DDMOST (Double-Diffused MOS Transistor)



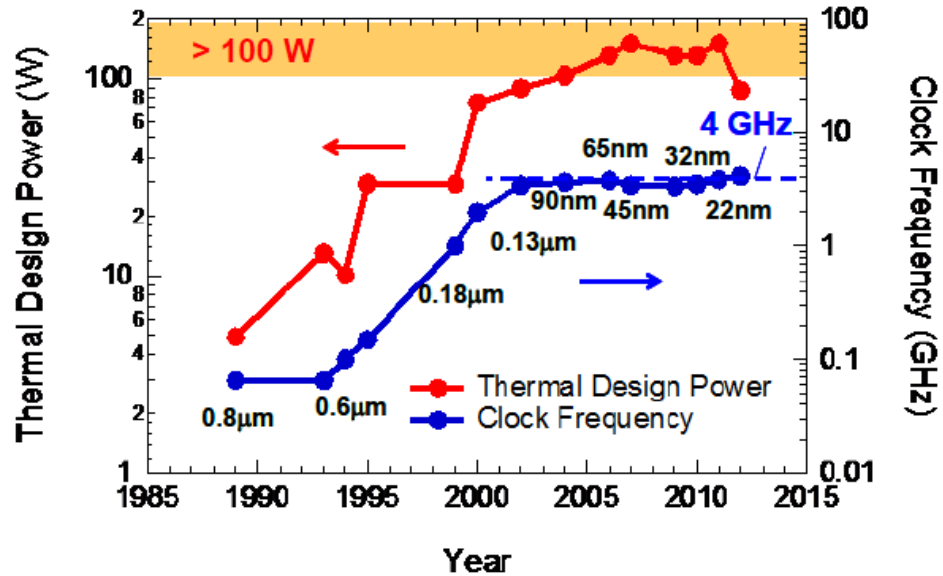
## Commercialisation

Siliconix (UK) delivered VMOS in 1975 as the first power FET in the marketplace.



<https://www.electronicdesign.com/content/article/21188215/then-and-now>

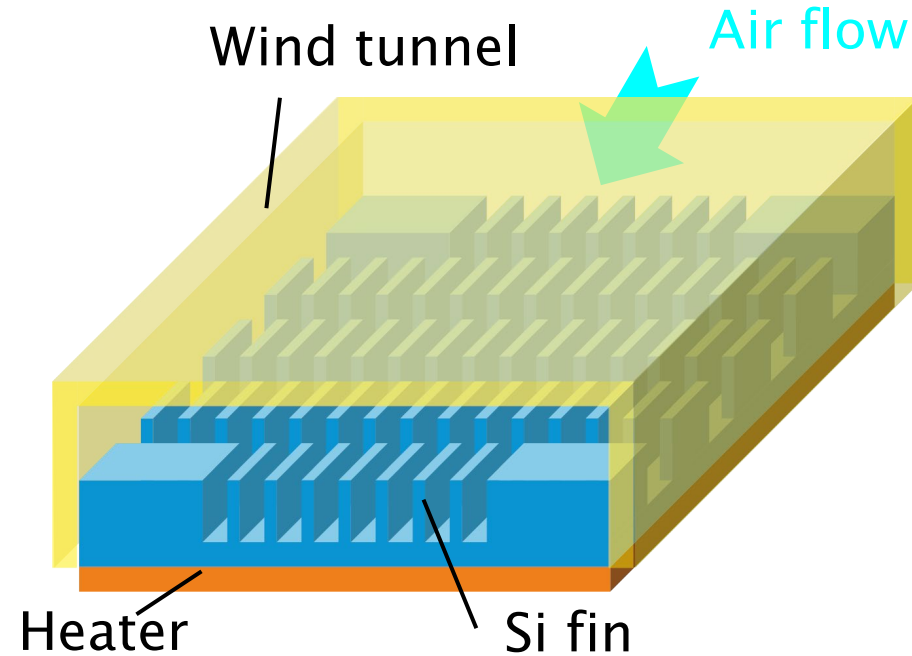
## TDP vs Frequency in ICs



- CPU clock frequency capped since early 2000.
- **The performance is limited by heat generation.**

## Silicon surface modified heat sinks

Y Zhang, Y Tsuchiya *et al.*, MNE2017, ICAN 2019



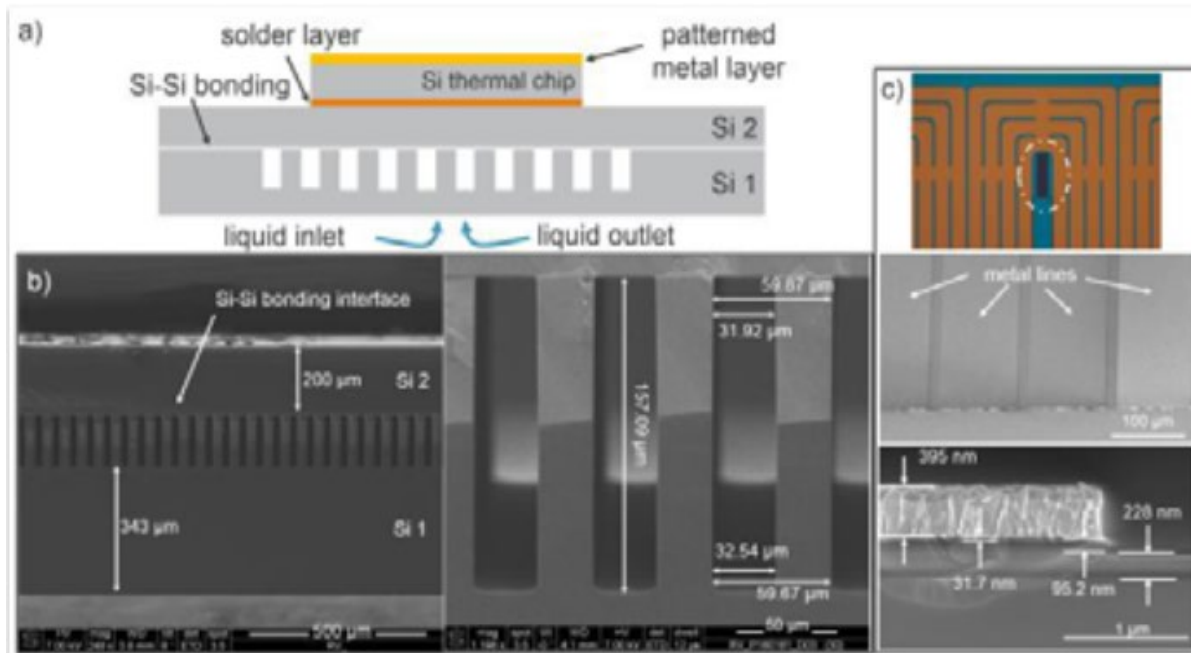
- Surface modification via micro- and nanofabrication technology to reduce the thermal resistance  $R_{\theta(s-a)}$ .

# Embedded cooling trends

Topic

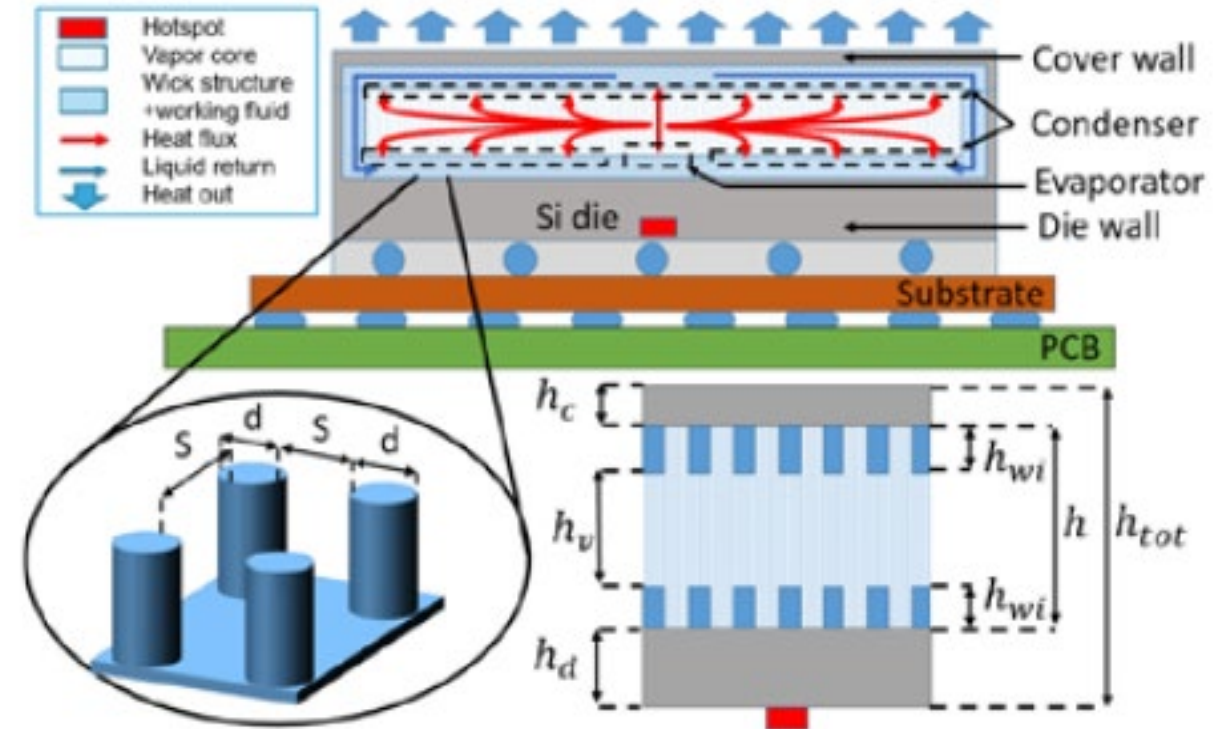
## Si microchannels

L Zhang *et al.*, Therminic 2018



## Si vapor chamber

Q Struss *et al.*, Therminic 2018



Application of silicon micro- and nanofabrication technologies for electronics cooling is under investigation in research level.

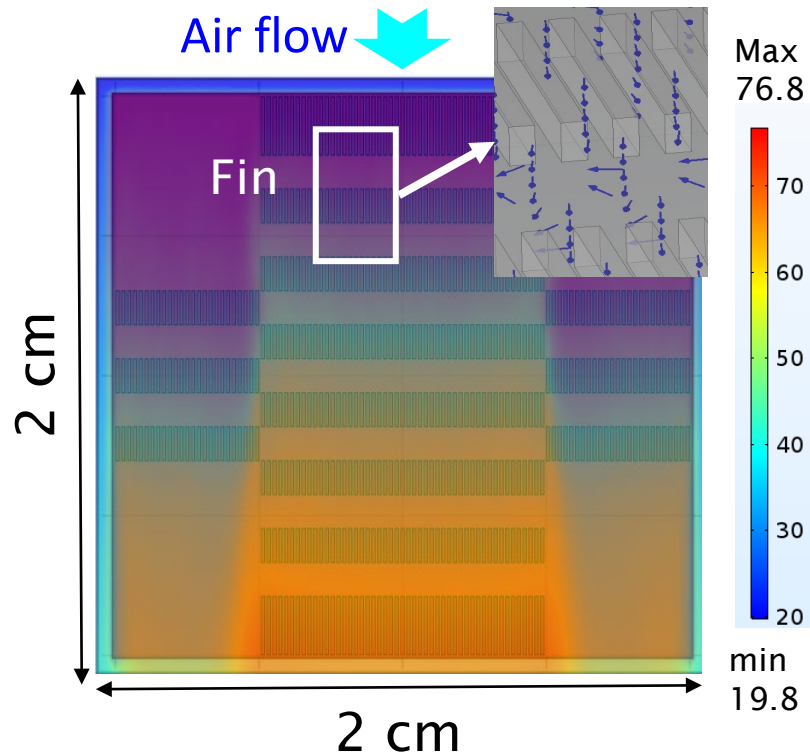


# COMSOL simulation results

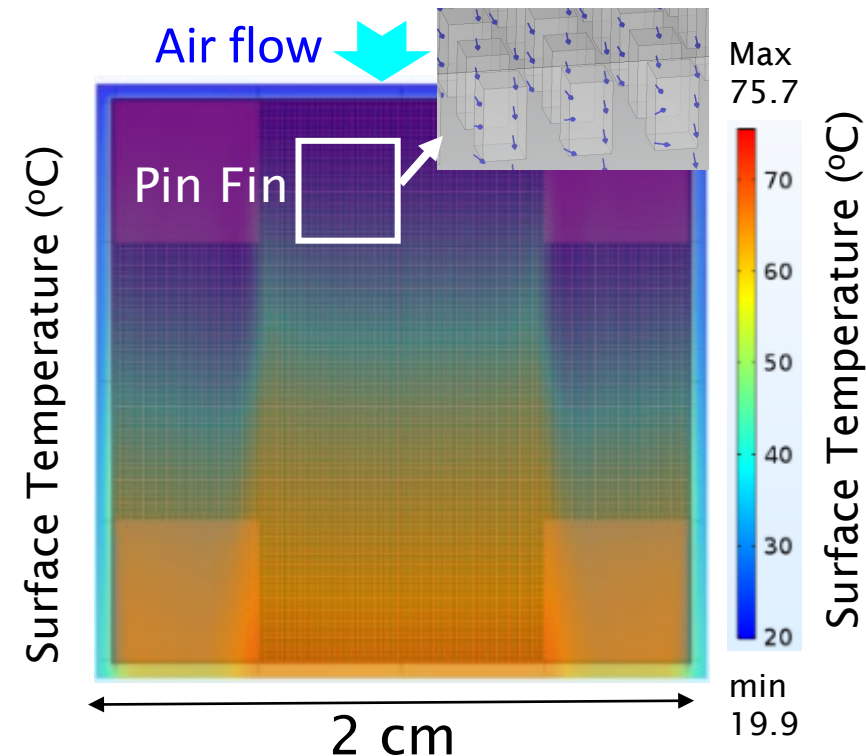
Topic

Inlet velocity: 3 m/s, Inlet  $T$ : 20 °C, Heater power: 3W

Y Zhang, PhD thesis



$T_{\max} = 76.8\text{ }^{\circ}\text{C}$



$T_{\max} = 75.7\text{ }^{\circ}\text{C}$

- Micro pin fin with larger surface area shows better.
- Further design optimisation possible (via movable fins, AI, etc)

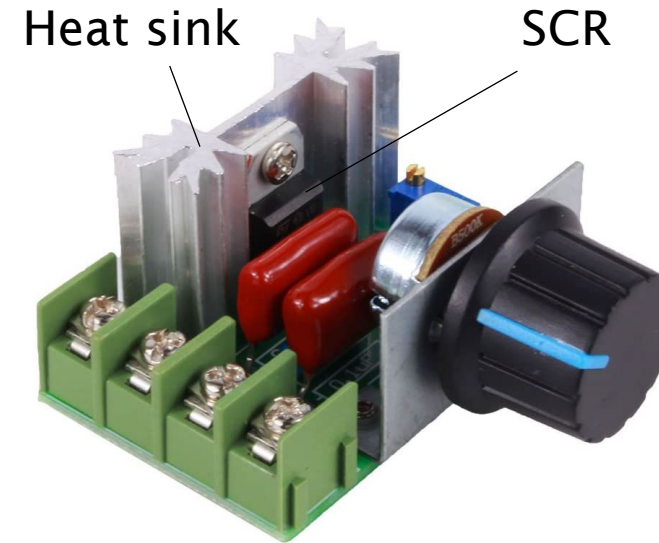
# AC voltage controllers - Products

Topic

<https://www.amazon.co.uk/>



220 V 4000 W voltage controller



50-220V LED Dimmer

Practical applications

Light dimmer, Fan controller, Motor controller, Temperature controller, etc.

# AC/DC converters

Topic

Source: Amazon, Farnell, Wikipedia

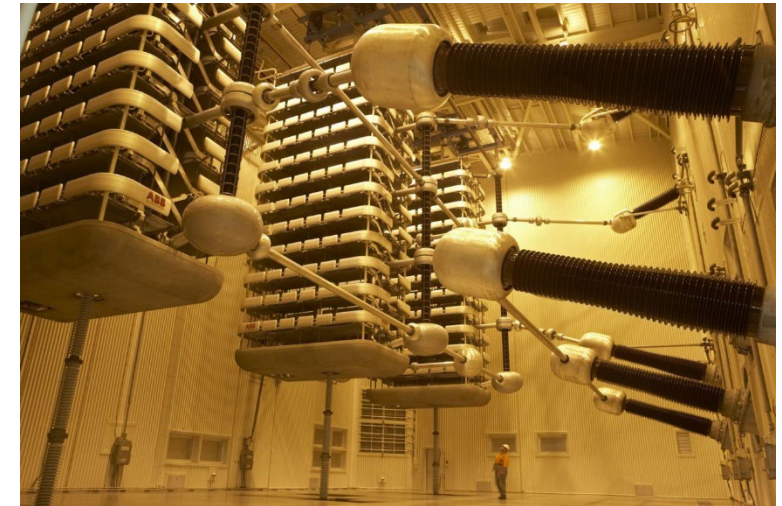
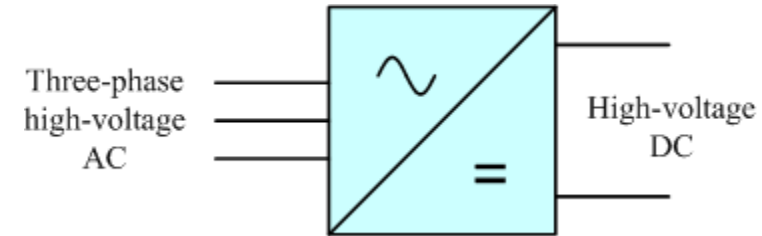


AC/DC adapter

AC 100-240V → DC 12V



Thyristor Bridge Rectifier Module,  
Three Phase, 1600 V



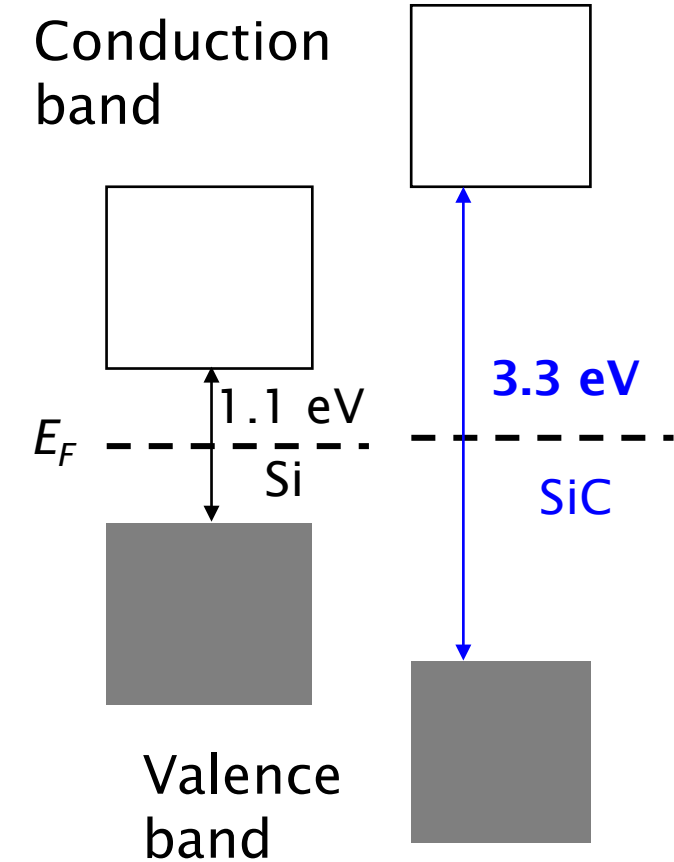
HVDC converter

~ 2000 MW, 900 kV

# Wide band-gap Semiconductors

Topic

J. Wang, IOP Conf. Series: Materials Science and Engineering 729 (2020) 012005



	Si	4H-SiC	GaN	$\beta$ -Ga <sub>2</sub> O <sub>3</sub>
Band gap, $E_g$ (eV)	1.1	3.3	3.4	4.5
Breakdown field, $E_c$ (MV/cm)	0.25	2.4	3.5	7
Relative permittivity, $\epsilon$	11.8	9.7	9.0	10-12
Electron mobility, $\mu_e$ (cm <sup>2</sup> /V.s)	1400	950	1200	200
Thermal conductivity (W/cm.K)	1.5	3.3 – 4.9	2	0.27
Baliga's Figure of Merit $\sim \epsilon\mu_e E_g^3$	1	340	870	>1,500

Promising materials for future power electronics and devices.



# Cycloconverter (CCV)

Topic

<https://library.e.abb.com/>

## ACS 6000c Cycloconverter



## Applications

- Ship propulsion
- Ball mills
- Mine hoists

For cases where load changes gradually.

50/60 Hz  $\rightarrow$  0 – 24/28 Hz

Speed and torque control of 1-27 MW

# DC-DC converter

Topic

<https://www.mouser.co.uk/>

<https://www.sunpower-uk.com/>

MEAN WELL

Input 9-36 V  
Output 12 V

Power 30W



~ £40

Sunpower Electronics

Input 200 – 750 V  
Output 12 or 24 V

1 kW

